



PATENT

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P2/DSM/BSVD/JW
#13/Response
(NES)
A total
366/12
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Huang

Serial No.: 09/270,039

Confirmation No.: 0424

Filed: March 16, 1999

**For: IN SITU DEPOSITION OF A LOW K
DIELECTRIC LAYER, BARRIER
LAYER, ETCH STOP AND ANTI-
REFLECTIVE COATING FOR
DAMASCENE APPLICATION**

Box AF
Assistant Commissioner for Patents
Washington, D.C. 20231

Group Art: 2823

Examiner: G. Fourson

CERTIFICATE OF MAILING

37 CFR 1.8

I hereby certify that this correspondence is being deposited on February 15, 2002 with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.

2/15/02
Date

Signature Kent R. Ricks

Dear Sir:

RESPONSE TO FINAL OFFICE ACTION DATED DECEMBER 18, 2001

In response to the Final Office Action dated December 18, 2001, having a shortened statutory period for response set to expire on March 18, 2002, please enter the following amendments and reconsider the claims pending in the application for reasons discussed below. Although Applicant believes that no fee is due in conjunction with this response, the Commissioner is hereby authorized to charge counsel's Deposit Account No. 20-0782/AMAT/2966P2/DD/BCVS/KMT, for any fees, including extension of time fees or excess claim fees, required to make this response timely and acceptable to the Office.

THE PENDING CLAIMS:

14. A method of forming a silicon carbide layer on a substrate, comprising:
introducing silicon, carbon, and a noble gas into a chamber;